



SEMICONDUCTOR

S8050LT1

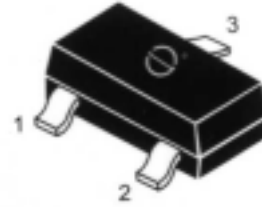
Shandong Yiguang Electronic Joint stock Co., Ltd

TECHNICAL DATA

NPN EPITAXIAL SILICON TRANSISTOR

- * Complement to S8550LT1
- * Collector Current :Ic= 500mA
- * High Total Power Dissipation :Pc=225mW

Package:SOT-23



ABSOLUTE MAXIMUM RATINGS at Ta=25

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	40	V
Collector-Emitter Voltage	Vceo	25	V
Emitter-Base Voltage	Veb	6	V
Collector Current	Ic	500	mA
Collector Dissipation Ta=25 *	P _D	225	mW
Junction Temperature	T _j	150	
Storage Temperature	T _{stg}	-55-150	

PIN:	1	2	3
STYLE			
NO.1	B	E	C

ELECTRICAL CHARACTERISTICS at Ta=25

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	40			V	Ic=100uA Ie=0
Collector-Emitter Breakdown Voltage#	BVceo	25			V	Ic= 1mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	6			V	Ie= 100uA Ic=0
Collector-Base Cutoff Current	Icbo			100	nA	Vcb= 35V Ie=0
Emitter-Base Cutoff Current	Iebo			100	nA	Veb= 6V Ic=0
DC Current Gain	Hfe ₁	45				Vce= 1V Ic= 5mA
DC Current Gain	Hfe ₂	85	160	300		Vce= 1V Ic= 50mA
DC Current Gain	Hfe ₃	30				Vce= 1V Ic= 500mA
Collector-Emitter Saturation Voltage	Vce(sat)		0.28	0.6	V	Ic= 500mA Ib= 50mA
Base-Emitter Saturation Voltage	Vbe(sat)		0.98	1.2	V	Ic= 500mA Ib= 50mA
Base-Emitter On Voltage	Vbe(on)		0.66	1	V	Vce= 1V Ic= 10mA
Output Capacitance	Cob		9		PF	Vcb=10V Ie=0 f=1MHz
Current Gain-Bandwidth Product	fT	100	190		MHz	Vce=10V Ic=50mA

* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25 .

Pulse Test : Pulse Width 300uS,Duty cycle 2%

DEVICE MARKING:

S8050LT1=A6



S8050LT1

